AMENDMENTS TO THE CLAIMS:

1. (Previously presented) A stent comprising a compound including Ti, N, C, or including Ti, N, O, or both, implanted at a depth within at least a region of a surface of the stent.

2. (Previously presented) The stent of Claim 21, wherein x is 1 and y is 1 or 2.

3. (Previously presented) The stent of Claim 21, wherein the depth of the implanted TiN_xO_y compound is not greater than about 2000 Å from the surface of the stent.

4. (Previously presented) The stent of Claim 21, additionally comprising a layer of TiN_xO_y compound deposited on the region of the surface of the stent where the TiN_xO_y compound is implanted.

5. (Original) The stent of Claim 4, wherein x is 1 and y is 1 or 2.

6. (Original) The stent of Claim 4, wherein the layer of TiN_xO_y compound is not more than about 48,000 Å in thickness.

7. (Original) The stent of Claim 1, wherein the stent is made from stainless steel.

8. (Original) The stent of Claim 1, wherein the surface is the tissue-contacting surface of the stent.

9. (Previously presented) The stent of Claim 1 comprising a layer of TiN_xO_y and a layer of Ti, N, or TiN disposed beneath the layer of TiN_xO_y.

10. (Original) The stent of Claim 9, wherein a region of the layer of TiN_xO_y is implanted at a depth within a surface of the stent.

11. (Withdrawn) The stent of Claim 1 comprising a surface and a TiN_xC_y compound deposited on at least a region of the surface of the stent.

12. (Withdrawn) The stent of Claim 1 comprising a surface and a TiN_xC_y compound implanted at a depth within at least region of the surface of the stent.

13. (Previously presented) A method of modifying a surface of a stent, comprising implanting a compound including Ti, N, C, or including Ti, N, O, or both, at a depth within a surface of the stent.

14. (Previously presented) The method of Claim 22 wherein x is 1 and y is 1 or 2.

15. (Previously presented) The method of Claim 22 additionally comprising forming a layer of a TiN_xO_y compound on the surface of the stent where the TiN_xO_y compound is implanted.

16. (Original) The method of Claim 15, wherein x is 1 and y is 1 or 2.

17. (Original) The method of Claim 13, wherein the stent is made from stainless steel.

18. (Previously presented) The method of Claim 13, wherein prior to the act of implanting the compound including Ti, N, C, or including Ti, N, O, or both, within the surface of the stent, the method comprises implanting Ti or N within the surface of the stent.

19. (Original) A method of modifying a stent surface, comprising implanting Ti, N, or TiN into the surface of the stent and forming a layer of a TiN_xO_y compound over the areas where Ti, N, or TiN has been implanted.

20. (Withdrawn) A method of modifying a surface of a stent, comprising implanting a TiN_xC_y compound at a depth within a surface of the stent or depositing the compound on the surface of the stent.

21. (Previously presented) A stent comprising a TiN_xO_y compound implanted at a depth within at least a region of a surface of the stent.

22. (Previously presented) The method of Claim 13, comprising implanting a TiN_xO_y compound at a depth within a surface of the stent.

23. (New) A stent comprising a compound including Ti, N, C, or including Ti, N, O, or both, implanted by plasma reaction at a depth within at least a region of a surface of the stent.

24. (New) The stent of Claim 23 wherein the stent is made from stainless steel.

25. (New) The stent of Claim 23 wherein the surface is the tissue-contacting surface of the stent.

26. (New) The stent of Claim 23 comprising a layer of TiN_xO_y and a layer of Ti, N, or TiN disposed beneath the layer of TiN_xO_y.

27. (New) The stent of Claim 26 wherein a region of the layer of TiN_xO_y is implanted by plasma reaction at a depth within a surface of the stent.

28. (New) A stent comprising a TiN_xO_y compound implanted by plasma reaction at a depth within at least a region of a surface of the stent.

29. (New) The stent of Claim 28 wherein x is 1 and y is 1 or 2.

30. (New) The stent of Claim 28 wherein the depth of the implanted TiN_xO_y compound is not greater than about 2000 Å from the surface of the stent.

31. (New) The stent of Claim 28 additionally comprising a layer of TiN_xO_y compound deposited on the region of the surface of the stent where the TiN_xO_y compound is implanted.

32. (New) The stent of Claim 31 wherein x is 1 and y is 1 or 2.

33. (New) The stent of Claim 31 wherein the layer of TiN_xO_y compound is not more than about 48,000 Å in thickness.

34. (New) A stent comprising a TiN_xO_y compound implanted by plasma reaction at a depth within at least a region of a surface of the stent.

35. (New) A method of modifying a surface of a stent, comprising implanting by plasma reaction a compound including Ti, N, C, or including Ti, N, O, or both, at a depth within a surface of the stent.

36. (New) The method of Claim 35 additionally comprising forming a layer of a TiN_xO_y compound on the surface of the stent where the TiN_xO_y compound is implanted.

37. (New) The method of Claim 35 comprising implanting by plasma reaction a

TiN_xO_y compound at a depth within a surface of the stent.

38. (New) The method of Claim 36 wherein x is 1 and y is 1 or 2.

39. (New) The method of Claim 35 wherein x is 1 and y is 1 or 2.

40. (New) The method of Claim 35 wherein the stent is made from stainless steel.

41. (New) The method of Claim 35 wherein prior to the act of implanting the compound including Ti, N, C, or including Ti, N, O, or both, within the surface of the stent, the method comprises implanting Ti or N within the surface of the stent.

42. (New) The method of Claim 35 comprising implanting a TiN_xO_y compound at a depth within a surface of the stent.

43. (New) A method of modifying a stent surface, comprising implanting by plasma reaction Ti, N, or TiN into the surface of the stent and forming a layer of a TiN_xO_y compound over the areas where Ti, N, or TiN has been implanted.

44. (New) A method of modifying a surface of a stent, comprising implanting a TiN_xC_y compound at a depth within a surface of the stent or depositing the compound on the surface of the stent.